



P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

| V _{(BR)DSS} | R _{DS(on)} max | I _D T _A = +25°C (Note 6) |
|----------------------|-------------------------------|--|
| -100V | 150mΩ@ V _{GS} = -10V | -5.9A |
| -1007 | 190mΩ@ V _{GS} =-6V | -5.1A |

Description

This new generation trench MOSFET from Zetex features a unique structure combining the benefits of low on-resistance and fast switching, making it ideal for high efficiency power management applications.

Applications

- DC-DC Converters
- Power Management Functions
- Disconnect Switches
- Motor Control

Features and Benefits

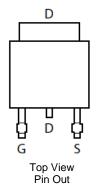
- Low On-Resistance
- Fast Switching Speed
- Low Threshold
- Low Gate Drive
- DPAK Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

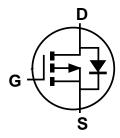
Mechanical Data

- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0 (Note 1)
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See diagram below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.315 grams (Approximate)



Top View





Equivalent circuit

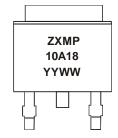
Ordering Information (Note 4)

| Ī | Part Number | Compliance | Case | Packaging |
|---|--------------|------------|-------|-------------------|
| | ZXMP10A18KTC | Standard | TO252 | 2,500/Tape & Reel |

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



ZXMP10A18 = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 10 = 2010) WW = Week (01 - 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

| Characteristic | | Symbol | Value | Units |
|---|---------------------------------------|------------------|-------|-------|
| Drain-Source Voltage | | V_{DSS} | -100 | V |
| Gate-Source Voltage | | V _{GSS} | ±20 | V |
| | $T_A = +25^{\circ}C$ (Note 6) | | -5.9 | |
| Continuous Drain Current | $T_A = +70^{\circ}C \text{ (Note 6)}$ | - | -4.7 | Α |
| | $T_A = +25^{\circ}C \text{ (Note 5)}$ | | -3.8 | |
| Pulsed Drain Current (Note 7) | | I _{DM} | -21.1 | А |
| Continuous Source Current (Body Diode) (Note 6) | | I _S | -10 | Α |
| Pulsed Source Current (Body Diode) (Note 7) | | I _{SM} | -21.1 | А |

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

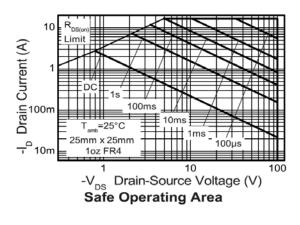
| Characteristic | | Symbol | Value | Units | |
|--|---------------------------------------|------------------|-------------|-------|--|
| | T + 25°C (Note 5) | | 4.3 | W | |
| | $T_A = +25^{\circ}C \text{ (Note 5)}$ | | 34.4 | mW/°C | |
| Total Power Dissipation (Note 5) Linear Derating Factor | T _A = +25°C (Note 6) | Ъ | 10.2 | W | |
| | | P _D | 81.3 | mW/°C | |
| | T _A = +25°C (Note 8) | | 2.17 | W | |
| | | | 17.4 | mW/°C | |
| | (Note 5) | | 29 | | |
| Thermal Resistance, Junction to Ambient | (Note 6) | $R_{\theta JA}$ | 12.3 | °C/W | |
| | (Note 8) | V - | 57.6 | | |
| Operating and Storage Temperature Range | | $T_{J_1}T_{STG}$ | -55 to +150 | °C | |

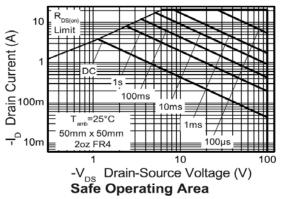
5. For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions.

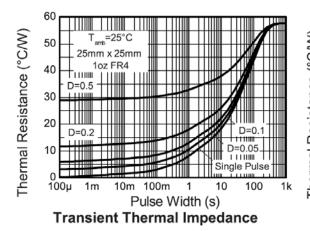
- 6. For a device surface mounted on FR4 PCB measured at t ≤10 sec.
- 7. Repetitive rating on 50mm x 50mm x 1.6mm FR4 PCB, D=0.02, pulse width=300µs pulse width limited by maximum junction temperature.

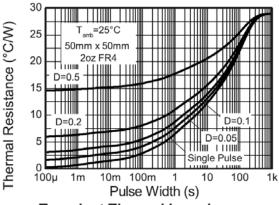
 8. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

Thermal characteristics







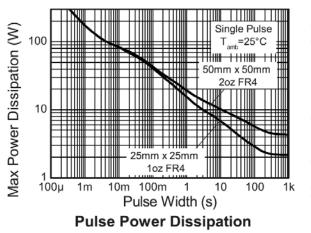


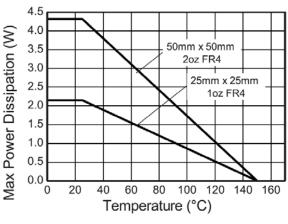
Transient Thermal Impedance

August 2014

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Derating Curve

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Min | Тур | Max | Unit | Test Condition | |
|--|----------------------|------|-------|------------|------|---|--|
| OFF CHARACTERISTICS | | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | -100 | _ | _ | V | $V_{GS} = 0V, I_D = -250\mu A$ | |
| Zero Gate Voltage Drain Current | I _{DSS} | | _ | -1 | μΑ | $V_{DS} = -100V, V_{GS} = 0V$ | |
| Gate-Source Leakage | IGSS | | _ | ±100 | nA | $V_{GS} = \pm 20V, V_{DS} = 0V$ | |
| ON CHARACTERISTICS | | | | | | | |
| Gate Threshold Voltage | V _{GS(th)} | -2 | _ | -4 | V | $V_{DS} = V_{GS}, I_{D} = -250\mu A$ | |
| Static Drain-Source On-Resistance (Note 9) | R _{DS (ON)} | _ | _ | 150 190 | mΩ | $V_{GS} = -10V, I_D = -2.8A$ | |
| | - (- , | | _ | 190 | | $V_{GS} = -6V, I_D = -2.4A$ | |
| Forward Transconductance (Notes 9 & 11) | g fs | | 6 | _ | S | $V_{DS} = -15V, I_{D} = -2.8A$ | |
| DYNAMIC CHARACTERISTICS (Note 11) | 1 | | 1 | | 1 | | |
| Input Capacitance | Ciss | | 1055 | _ | pF | ., 50,4,74, 0,4 | |
| Output Capacitance | Coss | | 90 | _ | pF | $V_{DS} = -50V, V_{GS} = 0V,$ f = 1MHz | |
| Reverse Transfer Capacitance | C _{rss} | | 76 | _ | pF | 1 - 11/11/12 | |
| SWITCHING CHARACTERISTICS (Notes 10 & 11 |) | | | | | | |
| Turn-On Delay Time | t _{d(on)} | _ | 4.9 | _ | | $V_{DS} = \text{-}50\text{V}, \ V_{GS} = \text{-}10\text{V}, \\ I_D = \text{-}1\text{A}, \ R_G = 6\Omega$ | |
| Rise Time | t _r | _ | 6.8 | _ | ns | | |
| Turn-On Delay Time | t _{d(off)} | | 33.9 | _ | 115 | | |
| Rise Time | t _f | _ | 17.9 | _ | | | |
| Total Gate Charge | Q_g | | 26.9 | _ | | $V_{DS} = -50V$, $V_{GS} = -10V$, $I_{D} = -2.8A$ | |
| Gate-Source Charge | Q_{gs} | | 3.9 | _ | nC | | |
| Gate-Drain Charge | Q_{gd} | | 10.2 | _ | | | |
| SOURCE-DRAIN DIODE CHARACTERISTICS | | | | | | | |
| Diode Forward Voltage (Note 9) | V_{SD} | | -0.85 | -0.95 | V | $T_J = +25^{\circ}C$, $V_{GS} = 0V$, $I_S = -3.5A$ | |
| Reverse Recovery Time (Note 11) | t _{rr} | | 49 | _ | ns | $T_J = +25^{\circ}C$, $I_S = -2.8A$, | |
| Reverse Recovery Charge (Note 11) | Q _{rr} | | 107 | _ | nC | di/dt=100A/μs, | |

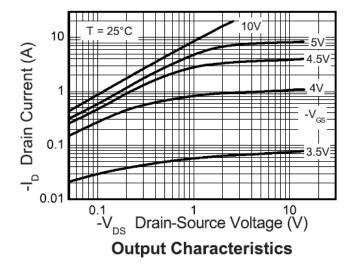
Notes: 9. Measured under pulsed conditions. Pulse width \leq 300 μ s; duty cycle \leq 2%.

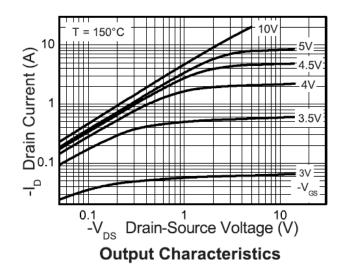
^{10.} Switching characteristics are independent of operating junction temperature.

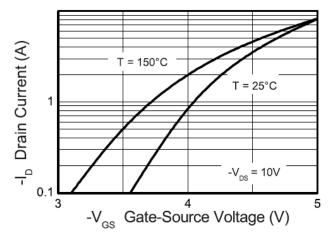
^{11.} For design aid only, not subject to production testing.

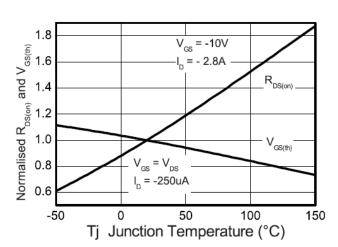


Typical characteristics



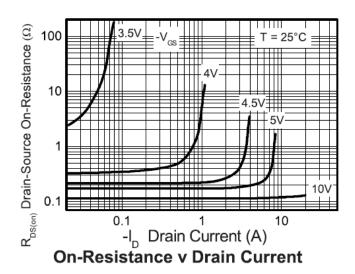


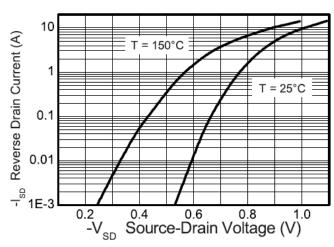




Typical Transfer Characteristics



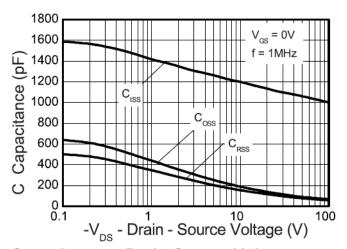




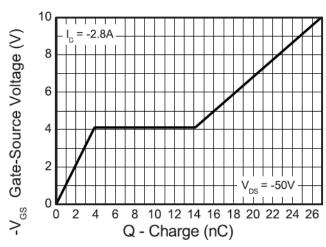
Source-Drain Diode Forward Voltage



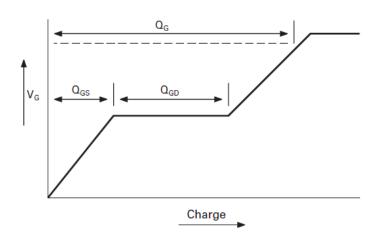
Typical characteristics



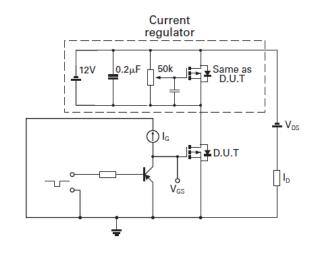
Capacitance v Drain-Source Voltage



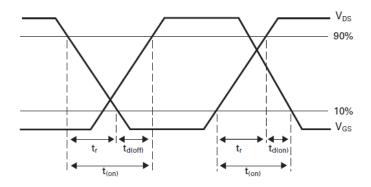
Gate-Source Voltage v Gate Charge



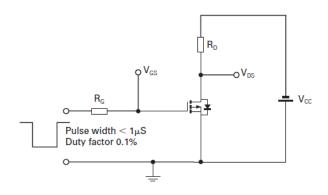
Basic gate charge waveform



Gate charge test circuit



Switching time waveforms

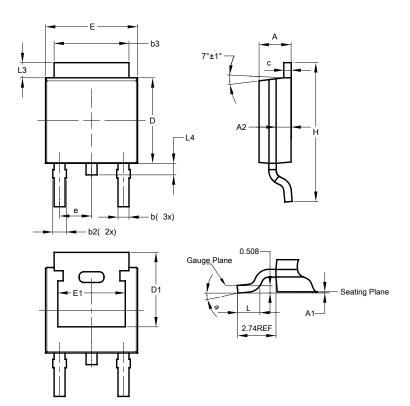


Switching time test circuit



Package Outline Dimensions

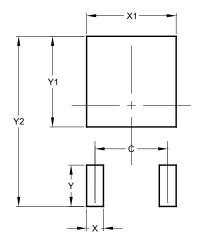
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



| TO252 (DPAK) | | | | | |
|----------------------|------|-------|-------|--|--|
| Dim | Min | Max | Тур | | |
| Α | 2.19 | 2.39 | 2.29 | | |
| A1 | 0.00 | 0.13 | 0.08 | | |
| A2 | 0.97 | 1.17 | 1.07 | | |
| q | 0.64 | 0.88 | 0.783 | | |
| b2 | 0.76 | 1.14 | 0.95 | | |
| b3 | 5.21 | 5.46 | 5.33 | | |
| С | 0.45 | 0.58 | 0.531 | | |
| D | 6.00 | 6.20 | 6.10 | | |
| D1 | 5.21 | - | - | | |
| е | - | - | 2.286 | | |
| Е | 6.45 | 6.70 | 6.58 | | |
| E1 | 4.32 | - | - | | |
| Н | 9.40 | 10.41 | 9.91 | | |
| L | 1.40 | 1.78 | 1.59 | | |
| L3 | 0.88 | 1.27 | 1.08 | | |
| L4 | 0.64 | 1.02 | 0.83 | | |
| а | 0° | 10° | - | | |
| All Dimensions in mm | | | | | |

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



| Dimensions | Value (in mm) | | | |
|------------|---------------|--|--|--|
| С | 4.572 | | | |
| Х | 1.060 | | | |
| X1 | 5.632 | | | |
| Υ | 2.600 | | | |
| Y1 | 5.700 | | | |
| Y2 | 10.700 | | | |



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